

Thyristor High Voltage, Phase Control SCR, 80 A

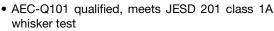


PRIMARY CHARACTERISTICS					
I _{T(AV)}	80 A				
V _{DRM} /V _{RRM}	1200 V				
V _{TM} (typ.)	1.18 V				
I _{GT}	100 mA				
T _J	-40 °C to +150 °C				
Package	TO-247AD 3L				
Circuit configuration	Single SCR				

LINKS TO ADDITIONAL RESOURCES



FEATURES





• 150 °C maximum operating junction temperature COMPLIANT

COMPLIANT HALOGEN

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-80TPS12L high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

MECHANICAL DATA

Case: TO-247AD 3L

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per

J-STD-002

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM} /V _{DRM}		1200	V		
On-state voltage	V_{T}	80 A, T _J = 125 °C, typical	1.18	V		
Average rectified forward current	I _{T(AV)}		80			
Maximum continuous RMS on-state current	I _{RMS}		126	Α		
Non-repetitive peak surge current	I _{TSM}	T _J = 150 °C, 10 ms sine	760			
Maximum rate of rise	dV/dt		1000	V/µs		
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-40 to +150	°C		

VOLTAGE RATINGS								
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	TYP. I _{RRM} /I _{DRM} AT 150 °C mA					
VS-80TPS12LHM3	1200	1300	20					



PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 103 °C, 180° conduction half sine v	wave	-	80	
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}			-	126	А
Dook one evels per repetitive curse current		10 ms sine pulse, rated V _{RRM} applied		-	640	
Peak, one-cycle non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied	Initial T _J =	-	760	
12t for fraince	I ² t	10 ms sine pulse, rated V _{RRM} applied	T _J maximum	-	2048	A ² s
I ² t for fusing	I-l	10 ms sine pulse, no voltage reapplied		-	2890	A-S
$I^2\sqrt{t}$ for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplie	d, T _J = 150 °C	-	28 900	A²√s
		80 A, T _J = 25 °C		1.23	1.38	
On state well-	V _T	160 A, T _J = 25 °C		1.48	1.68	V
On-state voltage		80 A, T _J = 125 °C		1.18	1.26	_ v
		160 A, T _J = 125 °C		1.50	1.62	
Low level value of threshold voltage	V _{T01}	T 150 %		-	0.85	V
High level value of threshold voltage	V _{T02}	T _J = 150 °C		-	0.96	V
Low level value of on-state slope resistance	r _{t1}	T _{.1} = 150 °C		-	4.50	mΩ
High level value of on-state slope resistance	r _{t2}	1J = 150 C		-	4.00	11152
Rate of rise of turned-on current	dl/dt	T_J = 150 °C, V_R < 800 V, I_T = 80 A, I_{gt} = 2 V_{GT} = 2.5 V, t_r < 100 ns, repetitive	200 mA,	-	200	A/μs
hate of fise of turned-off current	di/dt	T_J = 150 °C, V_R < 1000 V, I_T = 80 A, I_{gt} = 200 mA, V_{GT} = 2.5 V, t_r < 100 ns, non repetitive		-	500	ΑνμS
Holding current	I _H	Anada ayınılır. G.V. resistiya laad. T. QE °C		-	350	A
Latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C		-	500	mA
		T _J = 25 °C		25	100	μΑ
Reverse and direct leakage current	I _{RRM} /I _{DRM}	T _J = 125 °C		6	35	mA
		T _J = 150 °C		20	70	
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V_{DRM} , $R_{q-k} = open$			1000	V/µs

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Peak gate power	P _{GM}	10 ms sino puls	se, no voltage reapplied	-	10	W
Average gate power	P _{G(AV)}	To mis sine puis	se, no voltage reapplied	-	2.5] vv
Peak gate current	I _{GM}			-	2.5	Α
Peak negative gate voltage	-V _{GM}			-	10	
Described DO reterrellesse to bissess		T _J = -40 °C	Anode supply = 6 V resistive load	1.2	1.7	
	.,	T _J = 25 °C	Anode supply = 6 V resistive load	1.0	1.5	V
Required DC gate voltage to trigger	V_{GT}	T _J = 125 °C	Anode supply = 6 V resistive load	0.7	1.2	
		T _J = 150 °C	Anode supply = 6 V resistive load	0.6	1.1	
		T _J = -40 °C	Anode supply = 6 V resistive load	110	150	
Deguired DC gets to trigger		T _J = 25 °C	Anode supply = 6 V resistive load	60	100	mA
Required DC gate to trigger	I _{GT}	T _J = 125 °C	Anode supply = 6 V resistive load	25	50	
		T _J = 150 °C	Anode supply = 6 V resistive load	19	40	
DC gate voltage not to trigger	V_{GD}	T 150 %C V		-	0.20	V
DC gate current not to trigger	I _{GD}	T _J = 150 °C, V _{DRM} = 80 % rated value -		3	mA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Turn-on time	t _{gt}	$I_T = 80 \text{ A}, V_D = 50 \% V_{DRM}, I_{gt} = 300 \text{ mA}, T_J = 25 °C$	1.5	-	
Turn-off time	t _q	$I_{T} = 80 \text{ A, V}_{D} = 80 \text{ % V}_{DRM}, \text{dV/dt} = 20 \text{ V/}\mu\text{s, t}_{p} = 200 \mu\text{s}$ $I_{gt} = 100 \text{mA, dI/dt} = 10 \text{A/}\mu\text{s, V}_{R} = 100 \text{V, T}_{J} = 150 ^{\circ}\text{C}$	70	-	μs



THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	MAX.	UNITS
Maximum operating junction and storage temperature range				-40	150	°C
Maximum thermal resistance, junction	to case	R_{thJC}		-	0.31	
Maximum thermal resistance, junction to ambient		R_{thJA}		-	40	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth, and greased	0.	20	
Approximate weight				6 (0	.21)	g (oz.)
Mounting torque				6	(5)	kgf · cm
Mounting torque — maximum				12	(10)	(lbf · in)
Marking device			Case style TO-247AD 3L	8	0TPS12	2LH

ΔR_{thJ-HS} CONDUCTION PER JUNCTION											
DEVICE	s	SINE HALF-WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION				UNITS
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-80TPS12LHM3	0.042	0.047	0.054	0.057	0.059	0.038	0.049	0.051	0.054	0.057	°C/W

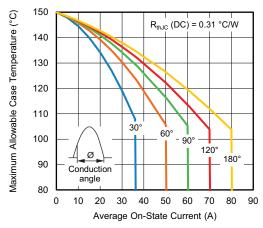


Fig. 1 - Current Rating Characteristics

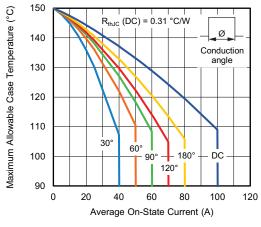


Fig. 2 - Current Rating Characteristics

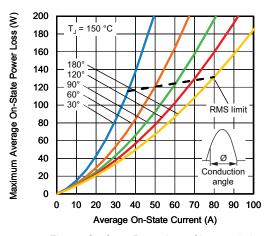


Fig. 3 - On-State Power Loss Characteristics

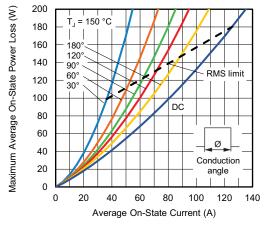


Fig. 4 - On-State Power Loss Characteristics

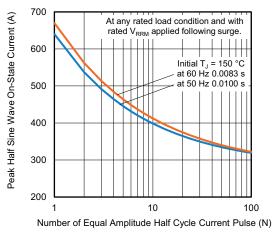


Fig. 5 - Maximum Non-Repetitive Surge Current

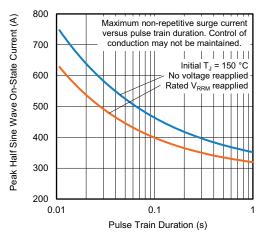


Fig. 6 - Maximum Non-Repetitive Surge Current

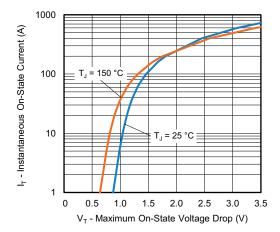


Fig. 7 - On-State Voltage Drop Characteristics

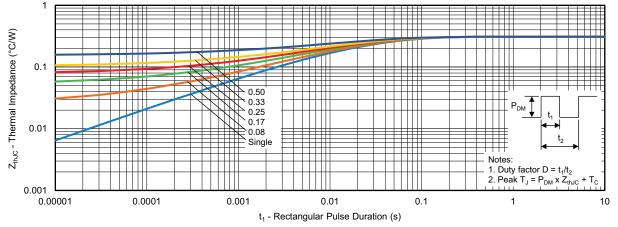
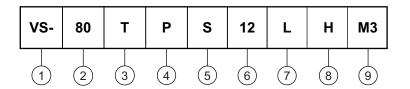


Fig. 8 - Maximum Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current code (80 = 80 A)

Circuit configuration:

T = thyristor

4 - P = TO-247 package

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage code (12 = 1200 V)

7 - Package L = long lead

8 - H = AEC-Q101 qualified

9 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (example)								
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-80TPS12LHM3	25	500	Antistatic plastic tubes					

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95626			
Part marking information	www.vishay.com/doc?95007			



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.